





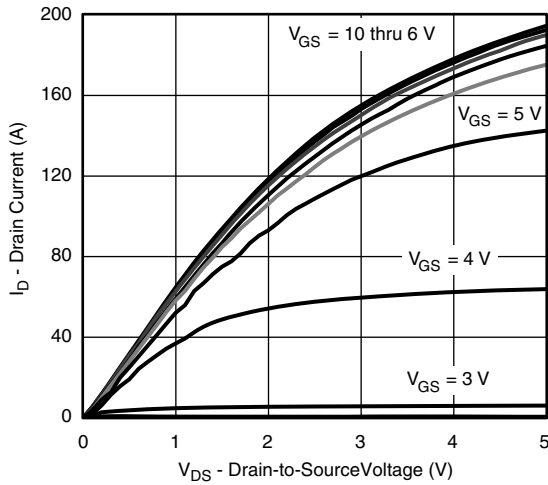
SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = - 250 μA	- 60			V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = - 250 μA		68		mV/°C
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>			- 5.2		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 1		- 3	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V			- 1	μA
		V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			- 10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 10 V	- 120			A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 30 A		0.0160	0.0195	Ω
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 20 A		0.0200	0.0250	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 50 A	20			S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = - 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz		3500		pF
Output Capacitance	C <sub>oss</sub>			390		
Reverse Transfer Capacitance	C <sub>rss</sub>			290		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 55 A		76	115	nC
				38	60	
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 55 A		16		
Gate-Drain Charge	Q <sub>gd</sub>			19		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		5.2		Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = - 2 V, R <sub>L</sub> = 2 Ω I <sub>D</sub> ≅ - 10 A, V <sub>GEN</sub> = - 10 V, R <sub>g</sub> = 1 Ω		10	15	ns
Rise Time	t <sub>r</sub>			7	15	
Turn-Off Delay Time	t <sub>d(off)</sub>			70	110	
Fall Time	t <sub>f</sub>			40	60	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 69	A
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				- 150	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = - 30 A		- 1	- 1.5	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 50 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C		45	68	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			59	120	nC
Reverse Recovery Fall Time	t <sub>a</sub>			29		ns
Reverse Recovery Rise Time	t <sub>b</sub>			16		

Notes:

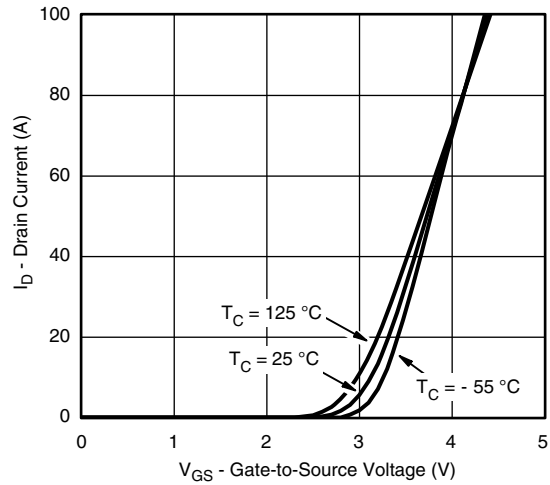
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

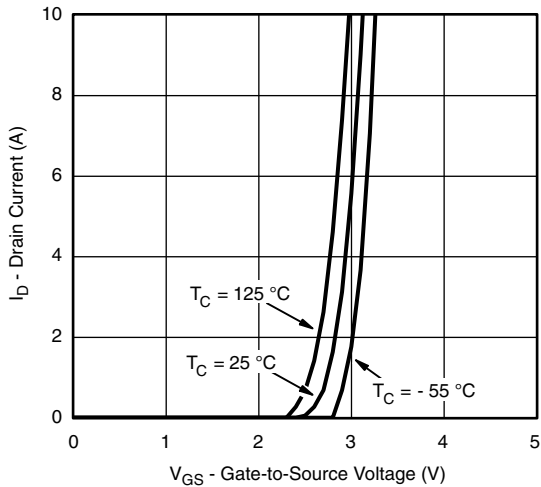
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



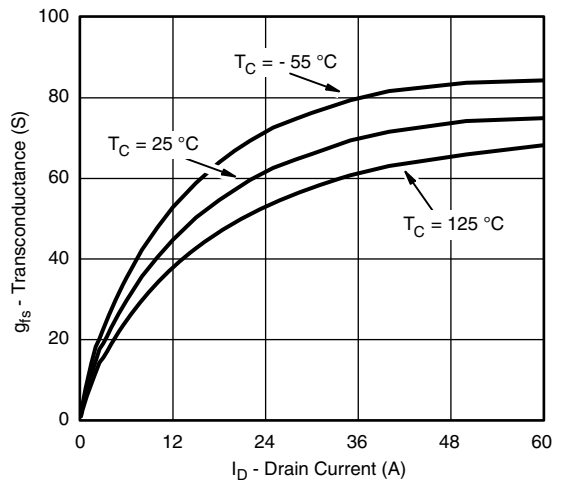
**Output Characteristics**



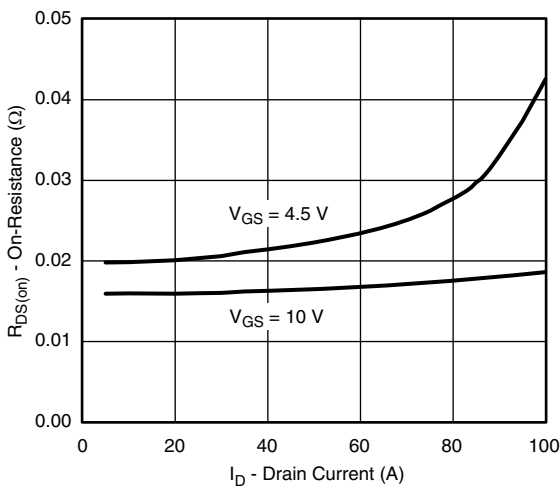
**Transfer Characteristics**



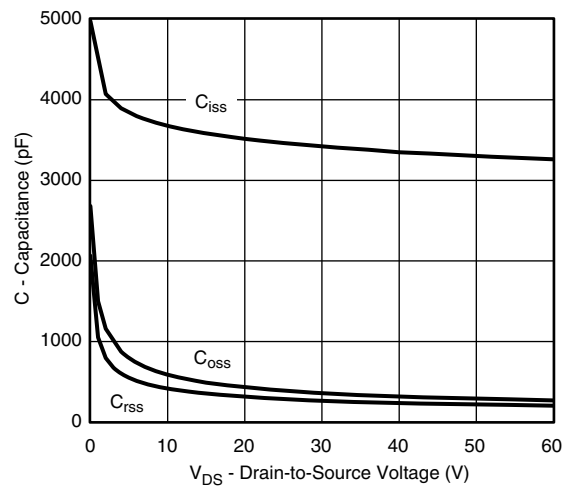
**Transfer Characteristics**



**Transconductance**

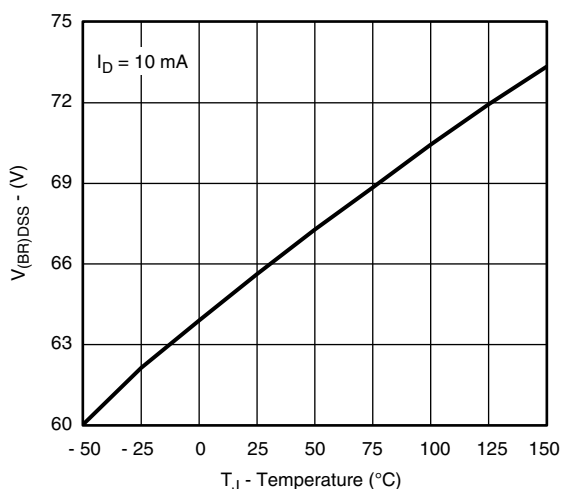
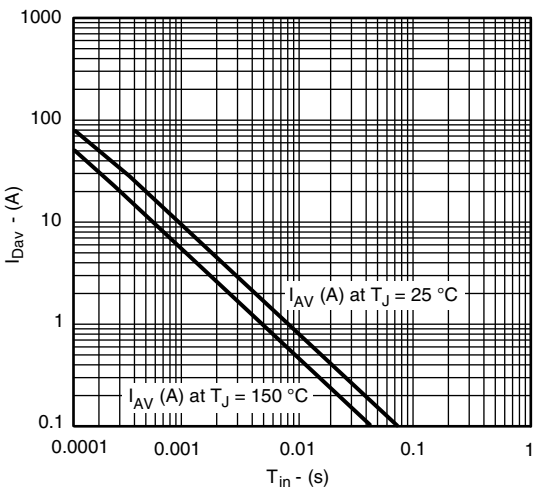
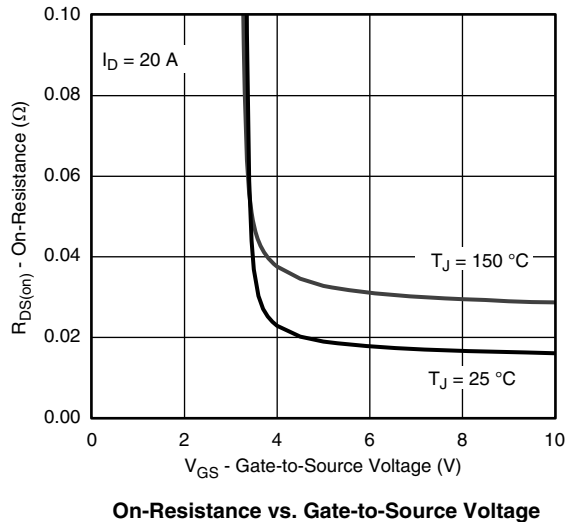
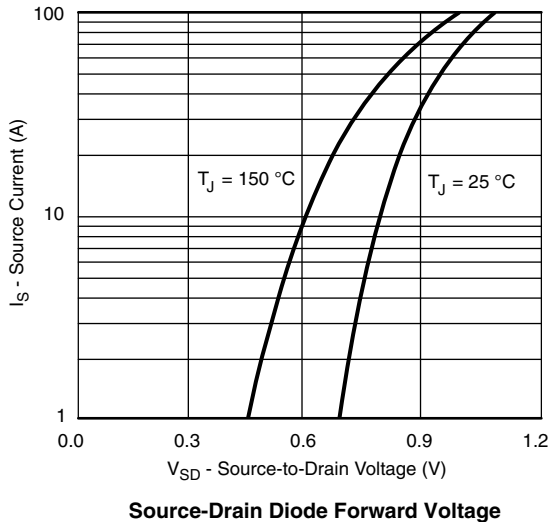
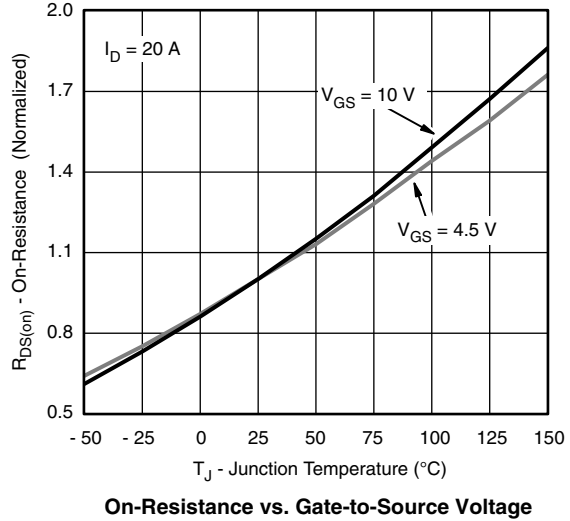
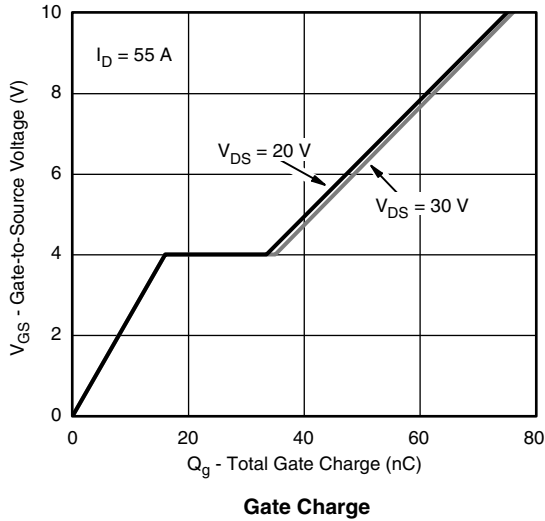


**On-Resistance vs. Drain Current**



**Capacitance**

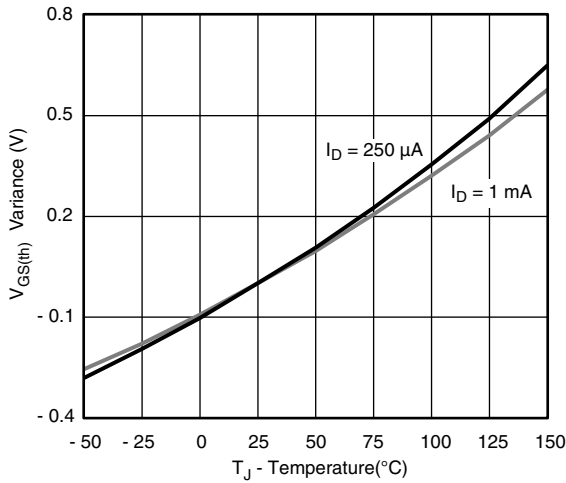
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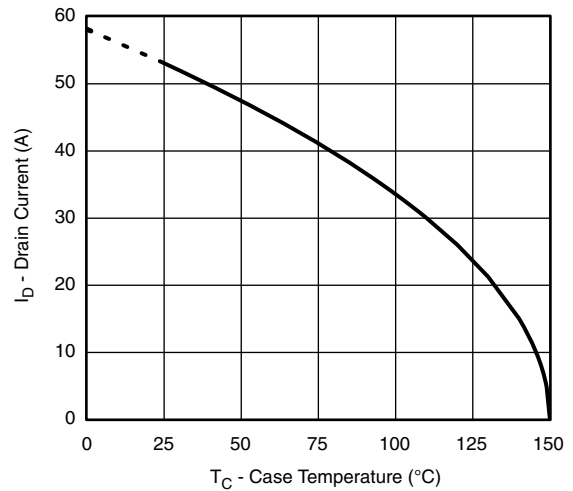
Single Pulse Avalanche Current Capability vs. Time

Drain-Source Breakdown Voltage vs. Junction Temperature

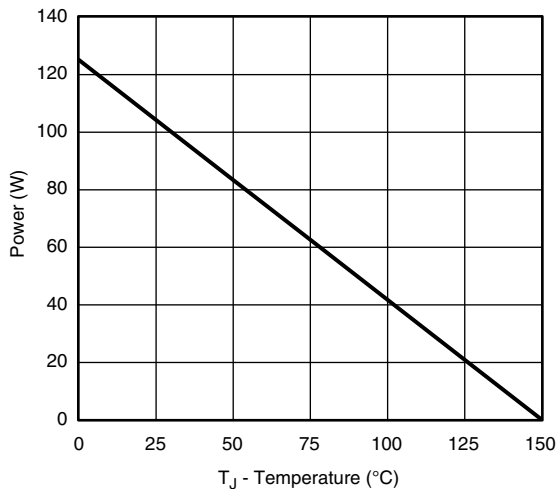
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



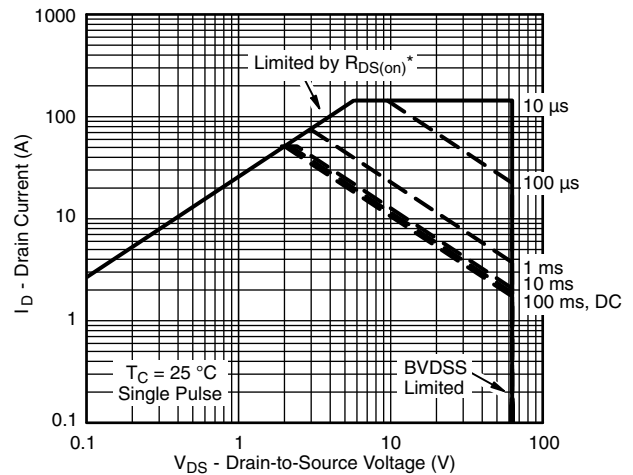
**Threshold Voltage**



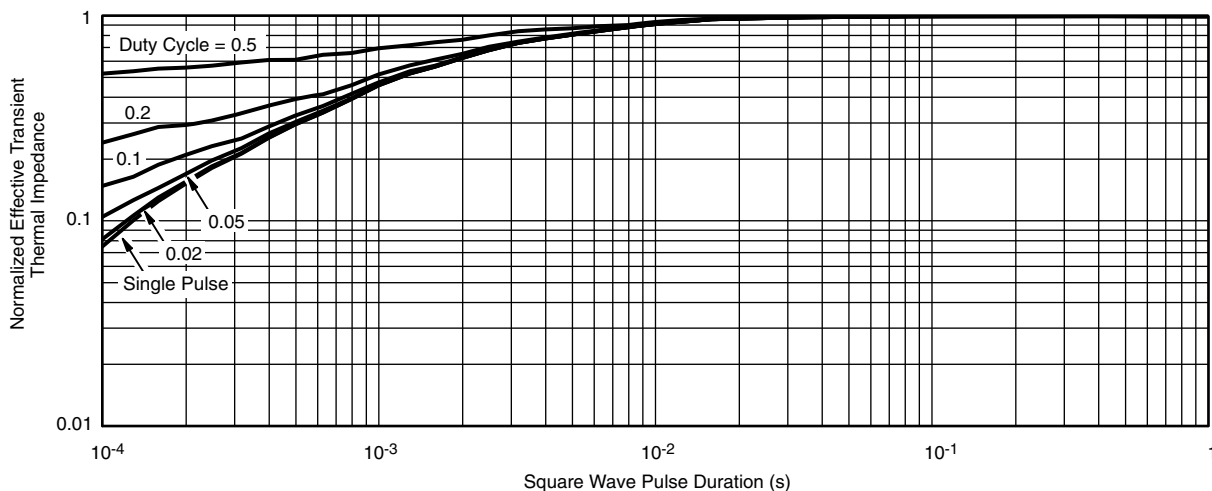
**Max. Drain Current vs. Case Temperature**



**Power Derating, Junction-to-Case**



**Safe Operating Area, Junction-to-Case**

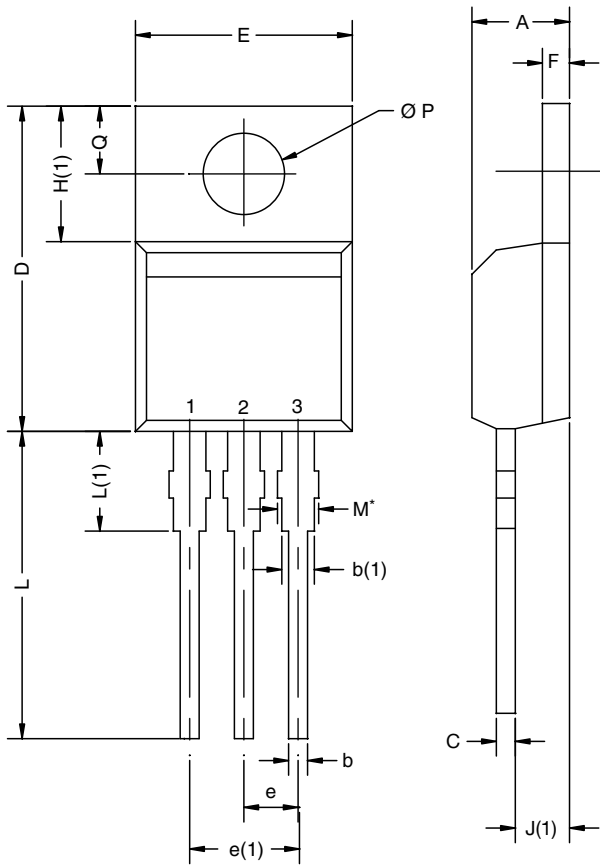


**Normalized Thermal Transient Impedance, Junction-to-Case**

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### TO-220AB

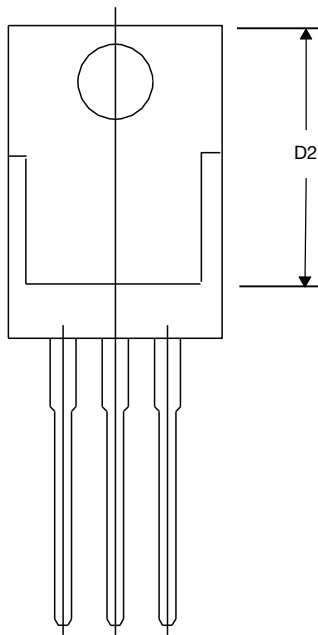


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: T14-0413-Rev. P, 16-Jun-14  
DWG: 5471

**Note**

\* M = 1.32 mm to 1.62 mm (dimension including protrusion)  
Heatsink hole for HVM





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